



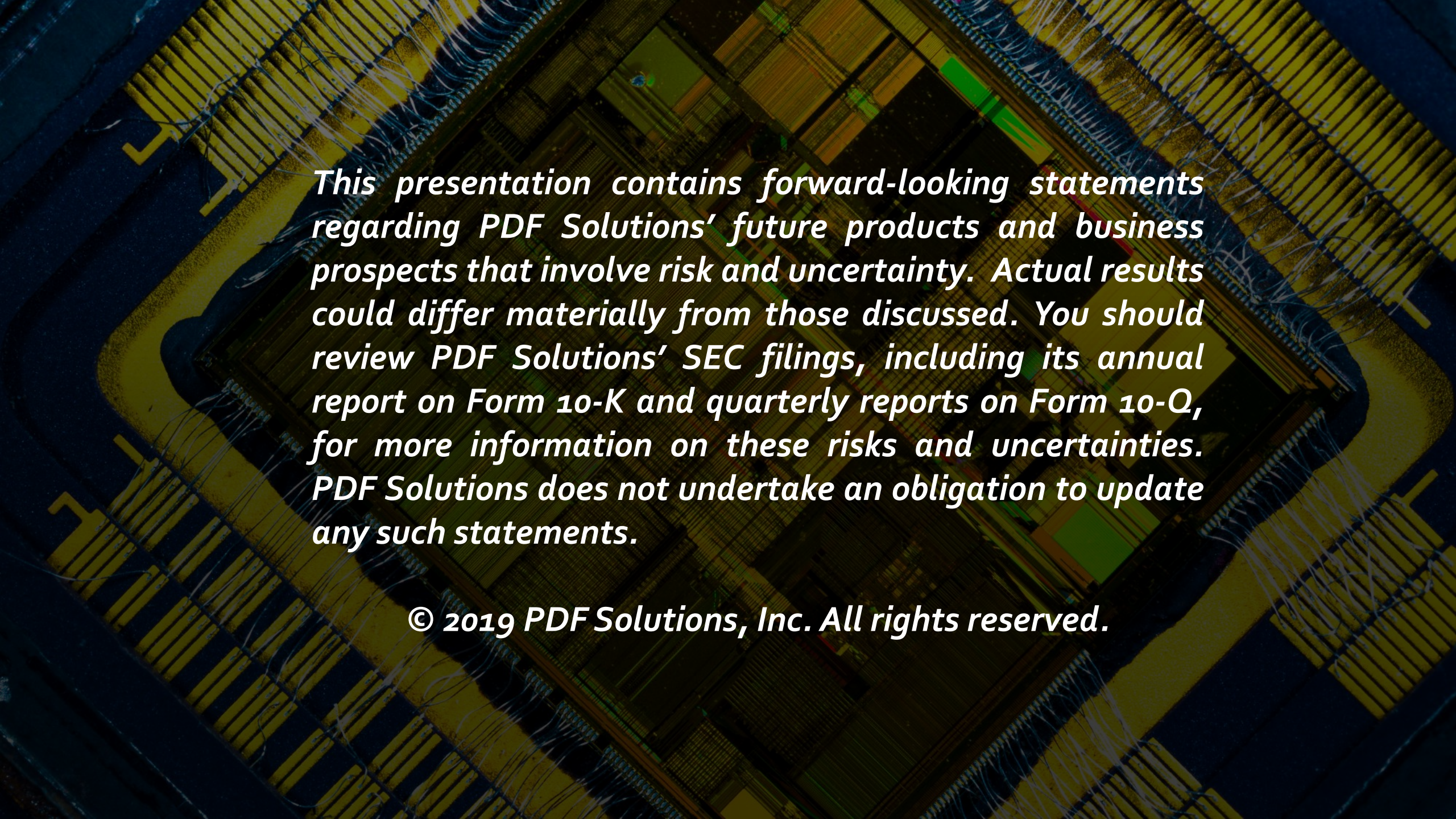
16th Annual PDF Solutions Users Conference

PDF/SOLUTIONS™

S1.4 – DFI™ and other New Sources of Data for Yield, Reliability and Process Control

October 15, 2019

Dennis Ciplickas, VP of Characterization Solutions

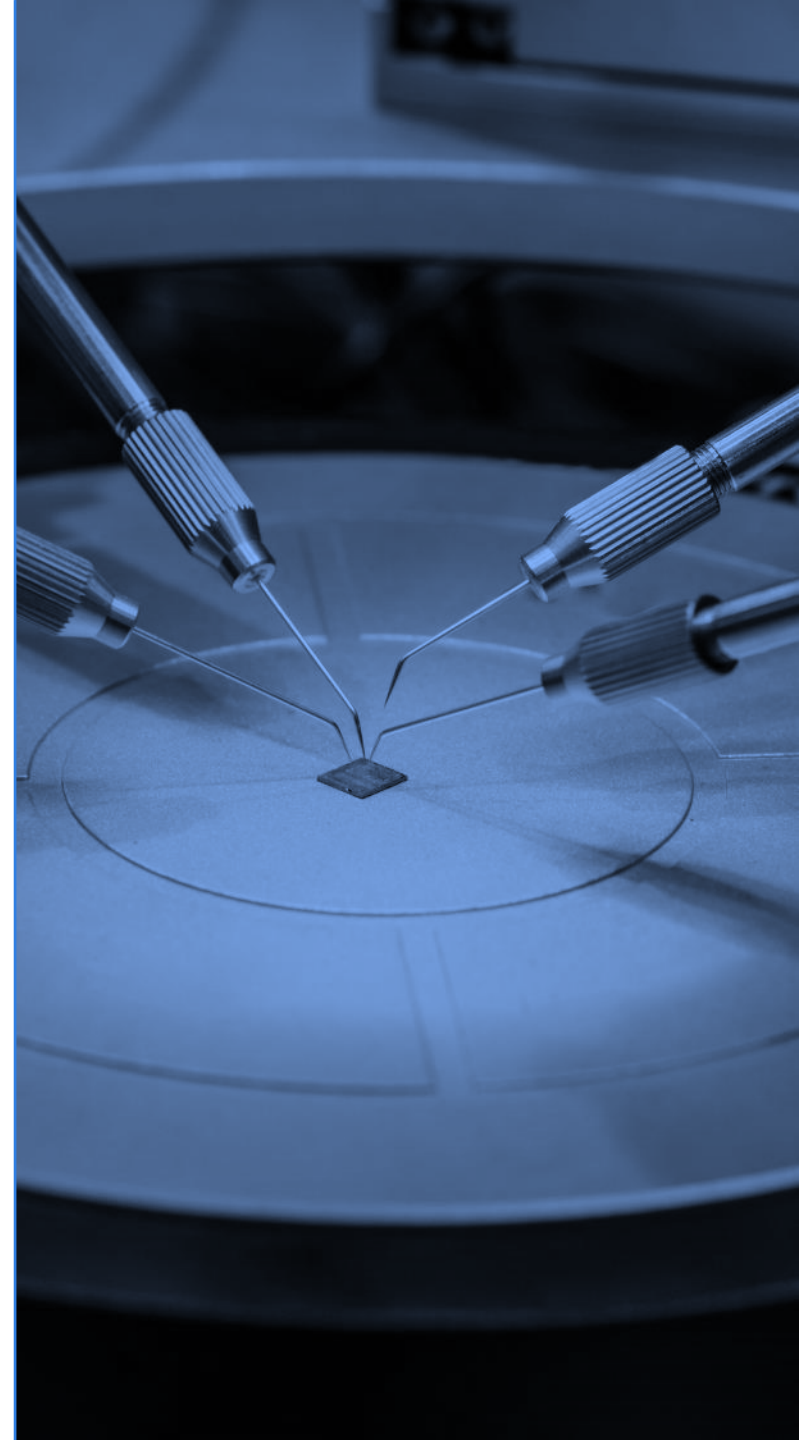
A high-magnification, top-down view of a complex electronic circuit board. The image shows a dense network of gold-colored conductive traces and pads. Numerous small, rectangular components, likely integrated circuits or capacitors, are soldered onto the board. The overall color palette is dominated by the metallic gold of the traces, with some darker, possibly black or dark green, areas representing the substrate or other components. The lighting creates a sense of depth, highlighting the intricate patterns of the circuitry.

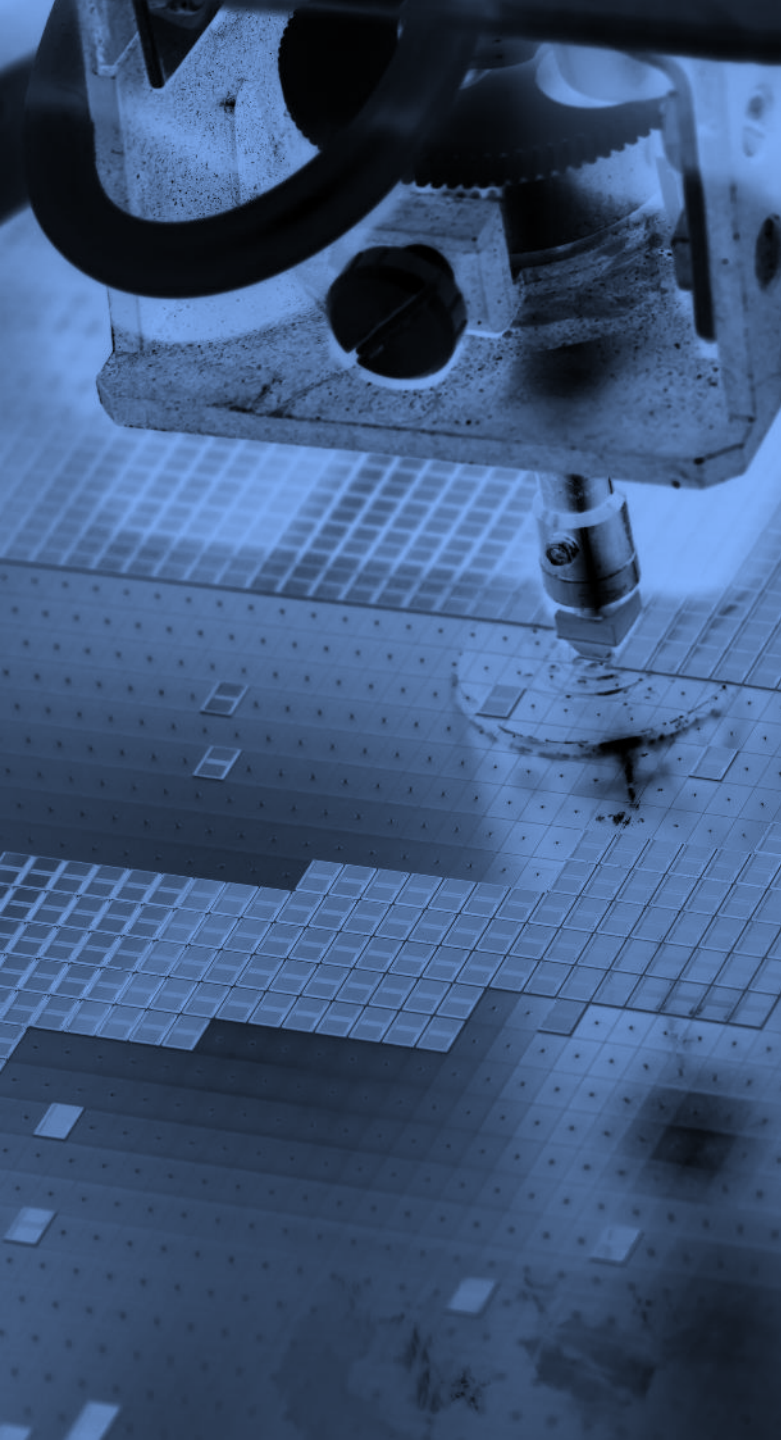
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Introduction

- PDF's business has always been based on data
- Deep insight from the unique data generated by our Characterization Vehicle® (CV®) Infrastructure is a key enabler for time-to-market in our Integrated Yield Ramp (IYR) business
- As PDF's analytics business has grown, so has the complexity of semiconductor systems, and the need for unique data persists
- We are extending, re-inventing and re-deploying IYR technology to create synergy with Exensio® analytics and new offerings for the evolving semiconductor ecosystem





Industry Trends

- Automotive
 - Advanced Driver-Assistance Systems (ADAS)
 - Aggressive move into advanced technology nodes
 - Functional Safety
 - Quality
- Data center
 - New computing architectures
 - CPU, GPU, AI, in-memory computing
 - New memory and storage architectures
 - SRAM, NVM, DRAM, NAND FLASH, HDD
 - Power consumption, Power vs. Performance vs. Reliability tradeoffs
 - Uptime, SLAs
- Mobile
 - Small, dense form factors with advanced packaging
 - InFO, CoWoS, FOWLP, EMIB, etc.
 - 5G networking creates technology platform with need for more storage

Quality Driver: Automotive Electronics

1950
1% of total vehicle cost is electronic



2010
30% of total vehicle cost is electronic



Est. 2030[†]
50% of total vehicle cost is electronic



5,000
semiconductor devices per
average car

1ppm failure
rate = 5 failures every
1,000 cars

10,000 cars manufactured per day
= **2 failures each hour!**

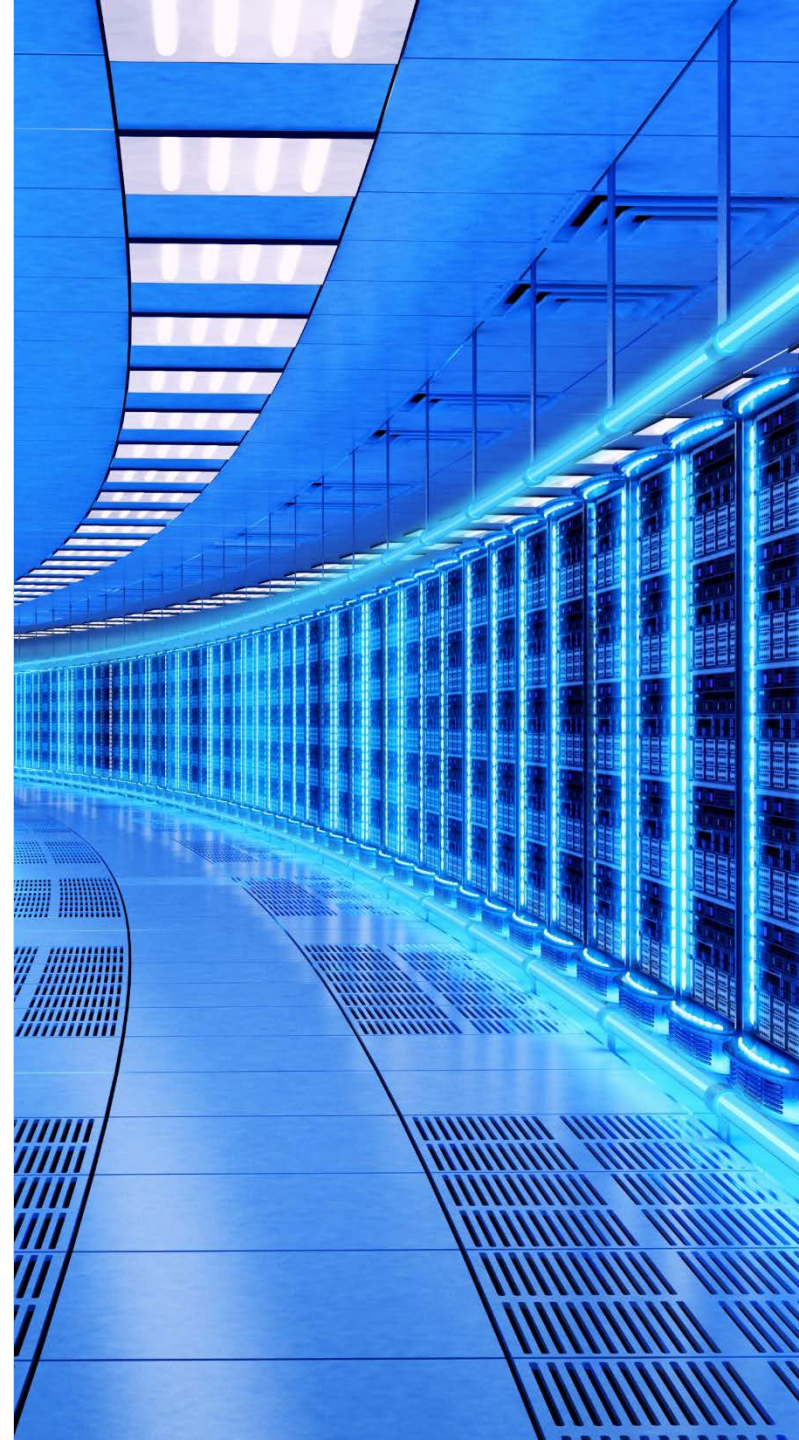
Key industries moving to ppb quality levels!

[†] statista.com

Power and Performance vs. Reliability

- Data Centers consume 3% of total electricity TODAY! †
 - Facebook: 100MW data center with 442,368 servers††
 - Facebook: average server utilization ~40% (265,420 unused servers) ††
- AI: Rat brain 518,400 processors, human brain 1000x more performance needed ††
- Poor Reliability leads to Silent Data Corruption, unacceptable latency and lost revenue
- New technology is needed to...
 - ...achieve 10x lower power to continue growth
 - ...enable reliability that meets aggressive SLA commitments

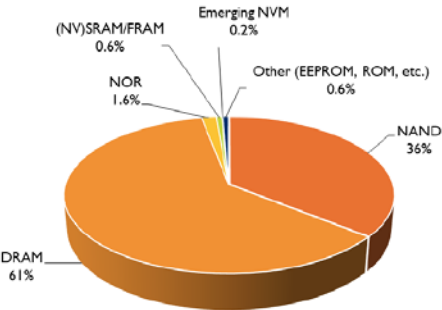
† [forbes.com](https://www.forbes.com) †† [FLASH Memory Summit 2018](#)



Memory Driver: Data Volume + New Computing Architectures

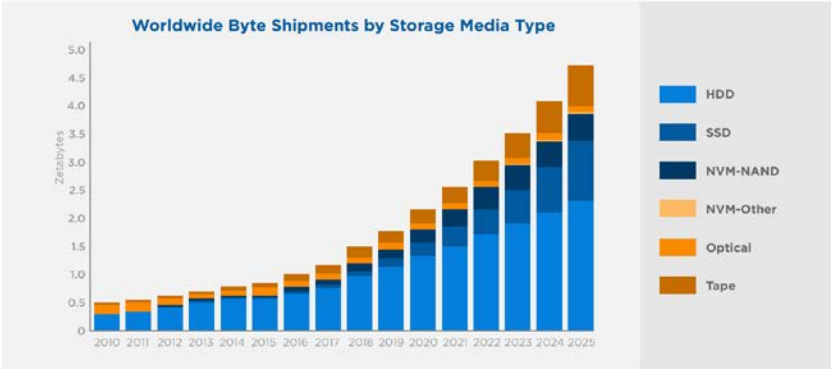
Flash Storage <ul style="list-style-type: none"> ○ 3D NAND ○ Cost/Bit scaling <ul style="list-style-type: none"> – Channel Hole Density – Vertical Scaling – Bits/Cell Increase 	Persistent memories <ul style="list-style-type: none"> ○ X-Point Memories ○ Power/Speed scaling ○ Cost/Bit scaling <ul style="list-style-type: none"> – Min X-Y dimensions scaling – Multi-layer 3D-stacking 	In-Memory Compute <ul style="list-style-type: none"> ○ Low-Power, Low-Latency embedded NVM ○ Multi-level, Analog Programming ○ Power/speed scaling ○ Cost reduction 	Embedded Memories <ul style="list-style-type: none"> ○ Low-Power, Low-Cost code, data storage for microcontrollers, IoT ○ Cost reduction ○ Reliability improvement ○ Power reduction
NEEDS: <ul style="list-style-type: none"> - Fast Node transition - High Yield - Innovation 	<ul style="list-style-type: none"> - 3D-stacking - Fast Node transition - High Yield 	<ul style="list-style-type: none"> - Fast development and co-integration with Logic - Performance/Yield - Cost reduction 	<ul style="list-style-type: none"> - Fast development and co-integration with Logic - Reliability/Yield - Cost reduction

2018 Memory Market - Breakdown by Technology



Total Stand-Alone Market in 2018 ≈ \$165 billions
Source: Yole, MRAM Developer Day, Flash Memory Summit 2019

Figure 10 - Worldwide Byte Shipments by Storage Media Type



Source: Data Age 2025, sponsored by Seagate with data from IDC Global DataSphere, Nov 2018

Key Takeaways

Reliability

- Safety, quality, and uptime are of paramount importance for new systems
- New chip technologies demand new sources of data to ensure reliability
- “Yesterday’s yield problem is tomorrow’s reliability problem”

Efficiency

- Rapid learning cycles are essential to creating a quality product
- Massive data collection is necessary to properly characterize reliability
- Quick, efficient data collection maximizes impact

Foresight

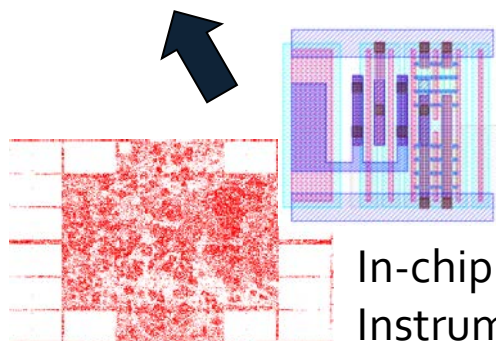
- Closing the loop “from fab to field” enables predictive models
- New, optimized and efficient operational flows are made possible with AI

PDF Differentiated Data for Reliability, Efficiency, and Foresight

Design-for-Inspection™ System



2nd generation
eProbe® 250
E-Beam HW

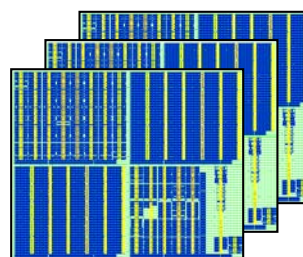


In-chip Product Instruments

Characterization Vehicle® System

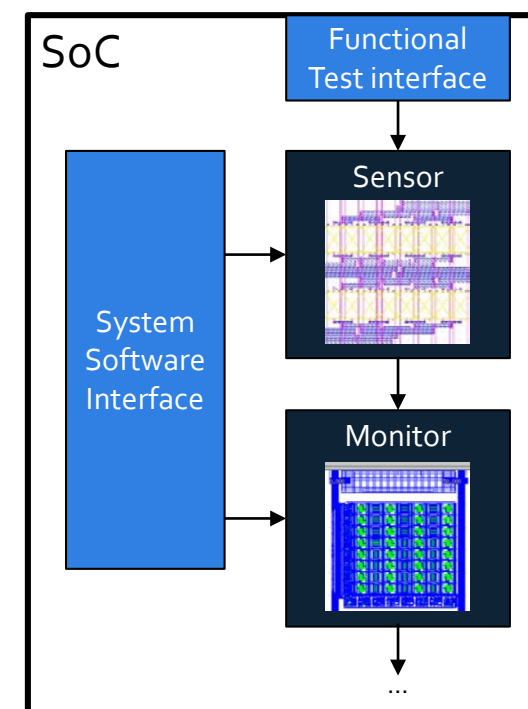


5th generation
pdFasTest®
E-Test HW



PDF CV®
Test Chips

CV® Core System



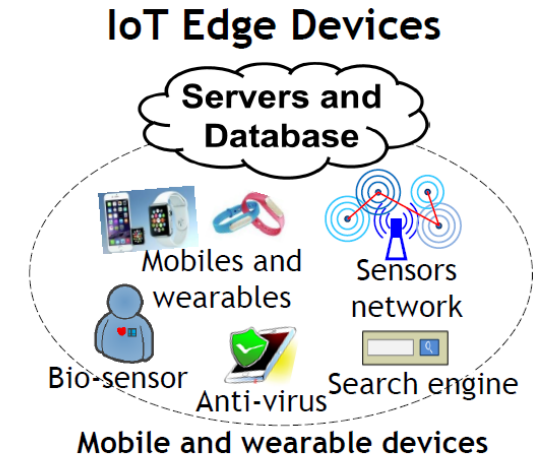
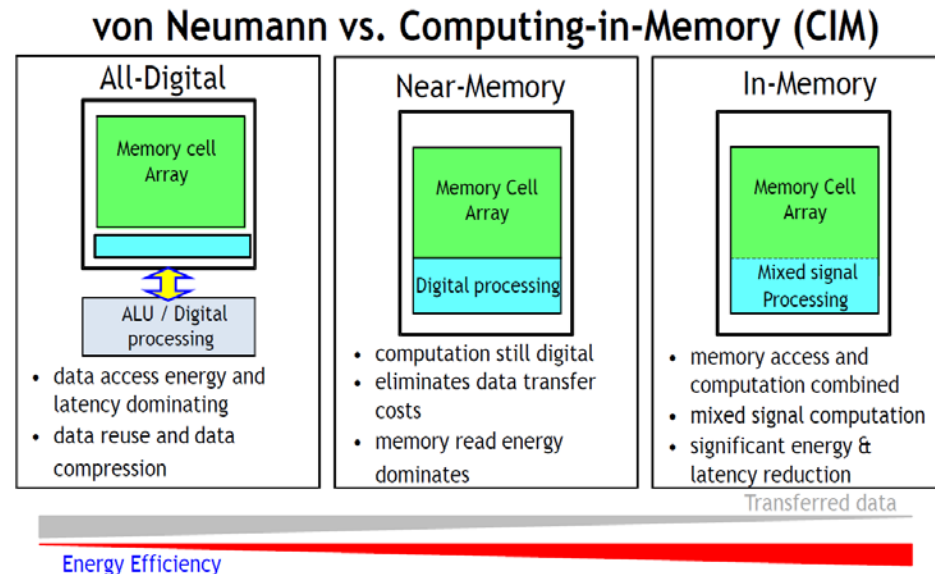
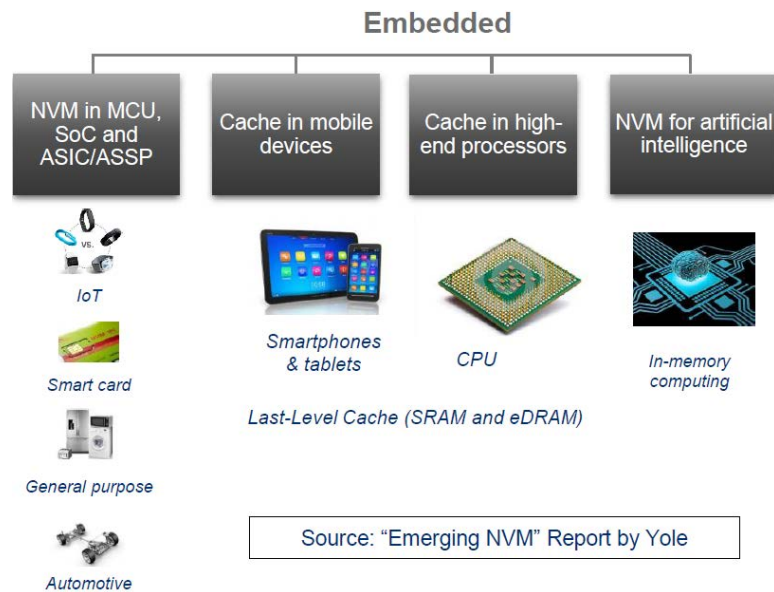
Inline

In-field

End-of-Line

Emerging Memories

- 62.7% of the total system energy is spent on Data movement[†] → **In-Memory Computing**
- Low latency Low-Power memory replacement SRAM → **MRAM for L3 Cache?**
- Emerging memories for Deep Learning → **On-chip High Density, Low Power solutions needed**
- Embedded memories for Automotive and IoT at 28nm and below → **Low power, High Reliability**

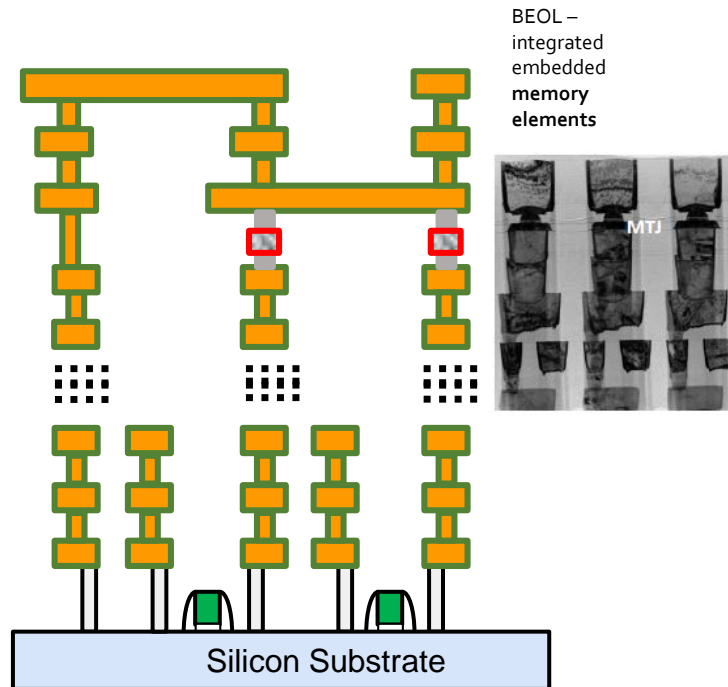


- Nonvolatile logics for frequent-off + instant-on devices

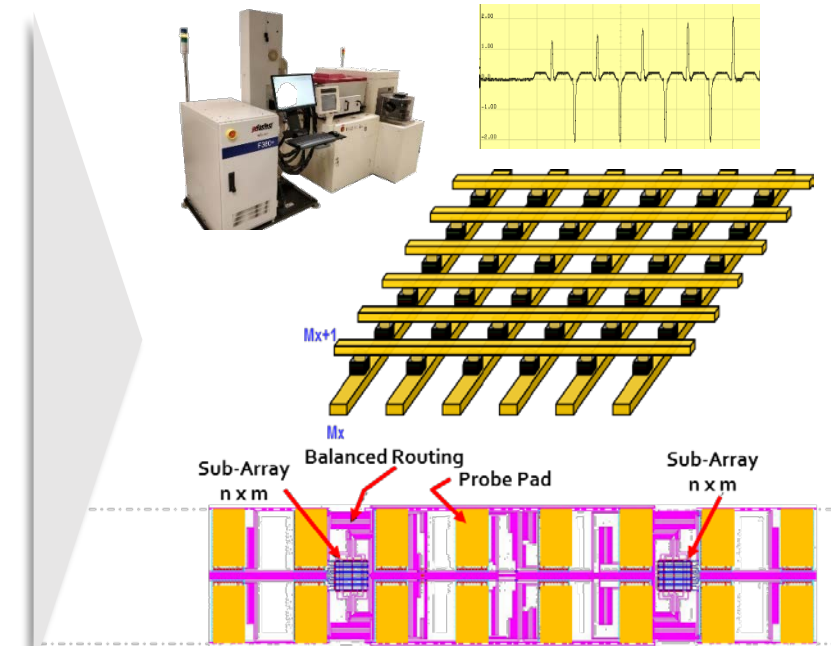
Source: VLSI Symposium on Circuits and Technology, Short Course, 2019

[†] [Google at ASPLOS18](#)

Enabling Emerging Memory Development



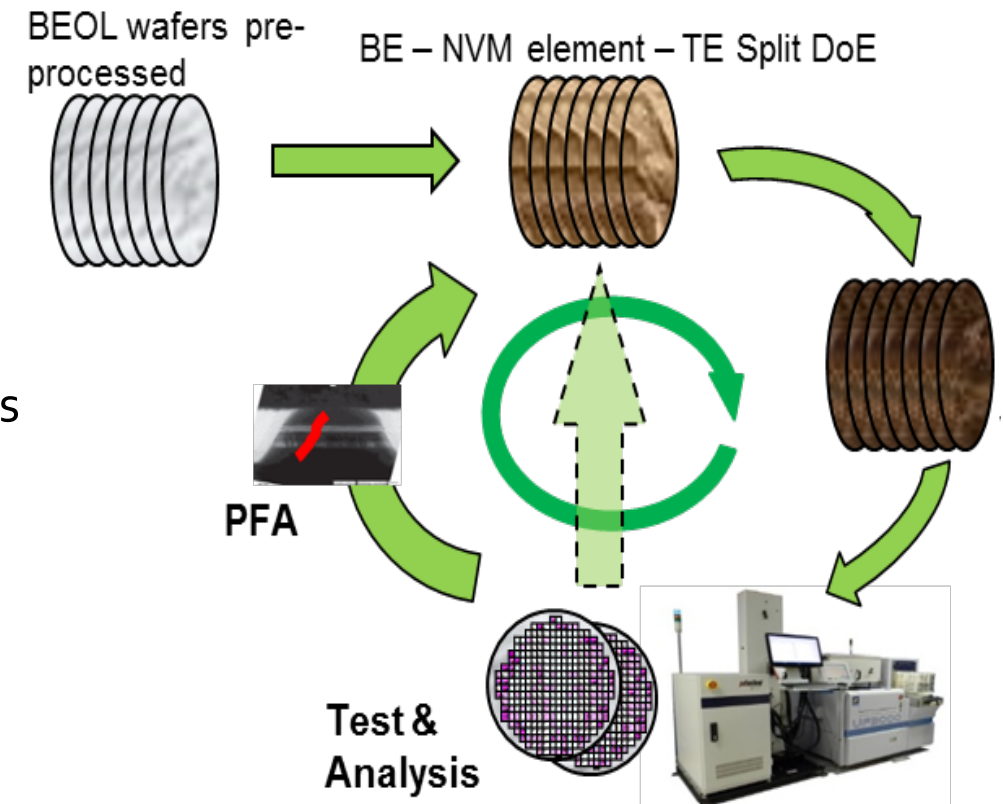
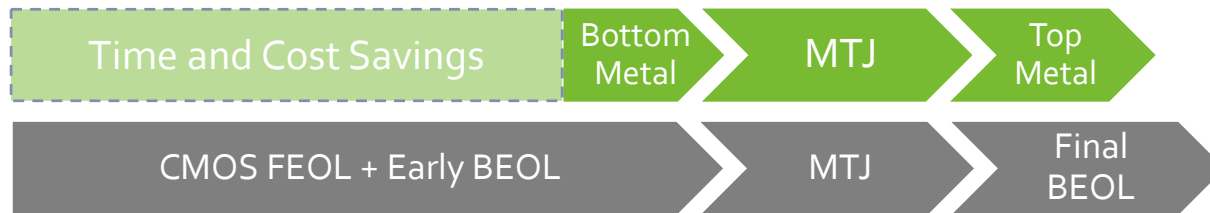
Full flow lots fabricate both back-end memory element and front-end selector devices → slow



Cross-point array with pdFasTest® parallel parametric pulse testing enables *efficient* learning

PDF Characterization System for Emerging Embedded Memories

- Unique Platform for BEOL-integrated Emerging Memories → MRAM, PCM, ReRAM
 - Innovative test structure and test method
 - Cross Point Array for high Bit statistics
 - pdFasTest® F380+ highly parallel pulsed parametric test
- Characterize millions of bits, millions of cycles in just hours



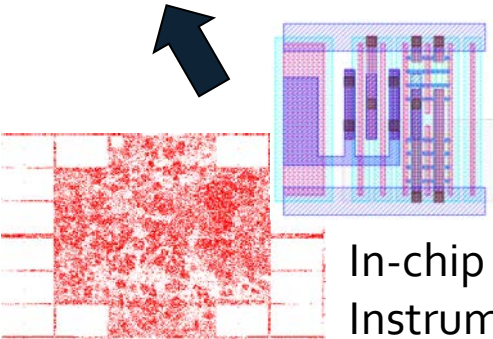
PDF's fast-learning characterization system *efficiently* enables the promise of emerging BEOL-embedded memories

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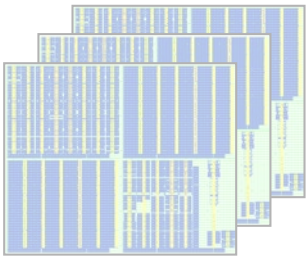


In-chip Product
Instruments

Characterization Vehicle® System

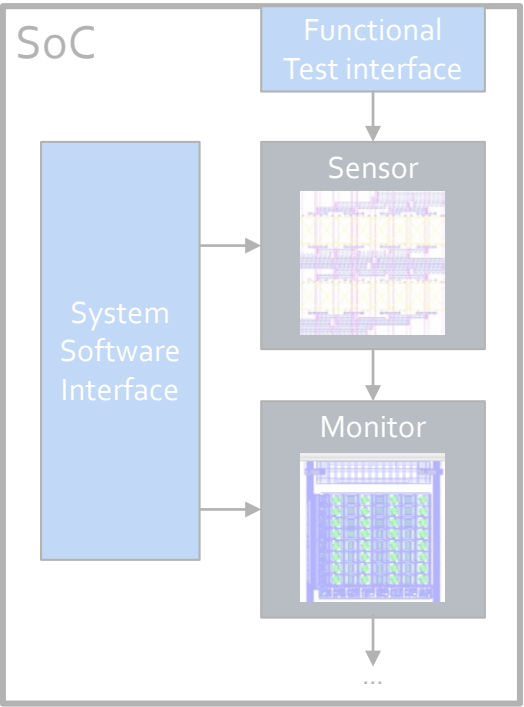


5th generation
pdFasTest®
E-Test HW



PDF CV®
Test Chips

CV® Core System

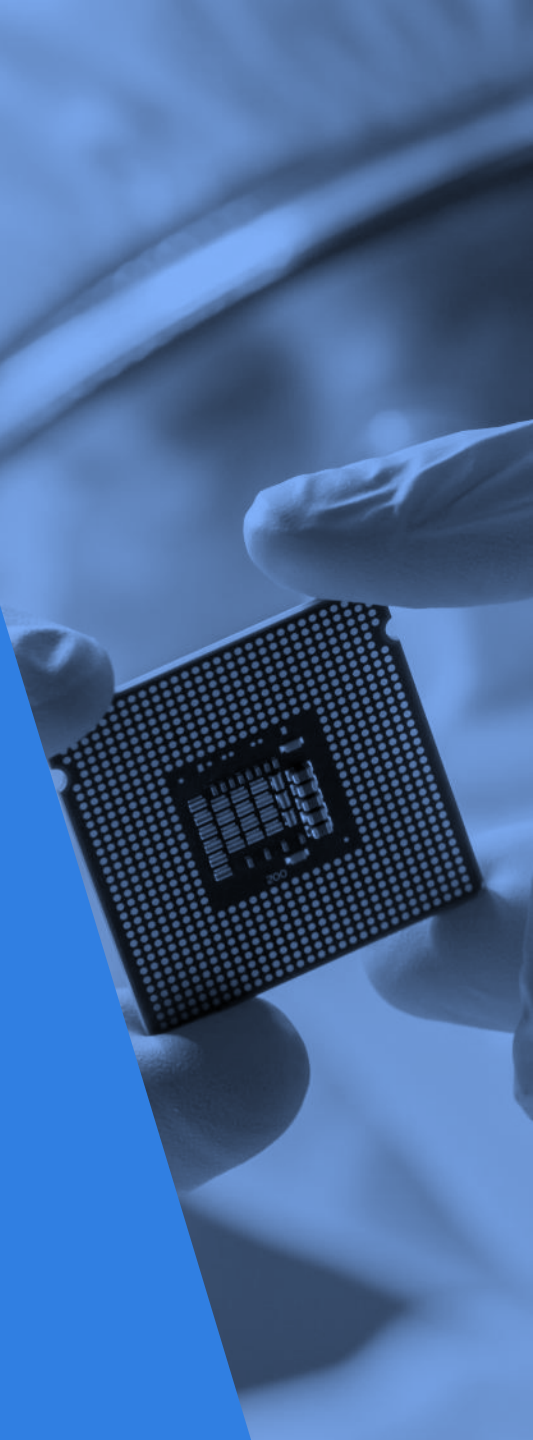


Inline

End-of-Line

In-field

Inputs from our Partners



- “Detect the Undetectable” → *Find electrically relevant defects buried inside 3D structures*
- “We are not late on a program because of functional yield, what kills us is we give the customer a chip, they package it, burn it in and figure out that there is a fundamental issue in a material stack or layout configuration. When that happens we lose 6 months to a year.”
- “We need a non-contacting in-line solution for every wafer”
- “Can you measure every die in-line and predict reliability?” → *Reliability Grading*

The Advantages of the DFI™ System

DFI Capability

- DFI is a contactless electrical test measurement using an e-beam system
- DFI measurement speed (raw): 100M's DUTs/hr today, Billions of DUTs/hr next
- Calibrated Leakage Value: pA to nA baseline, capture outliers >10x

DFI Fill Cell

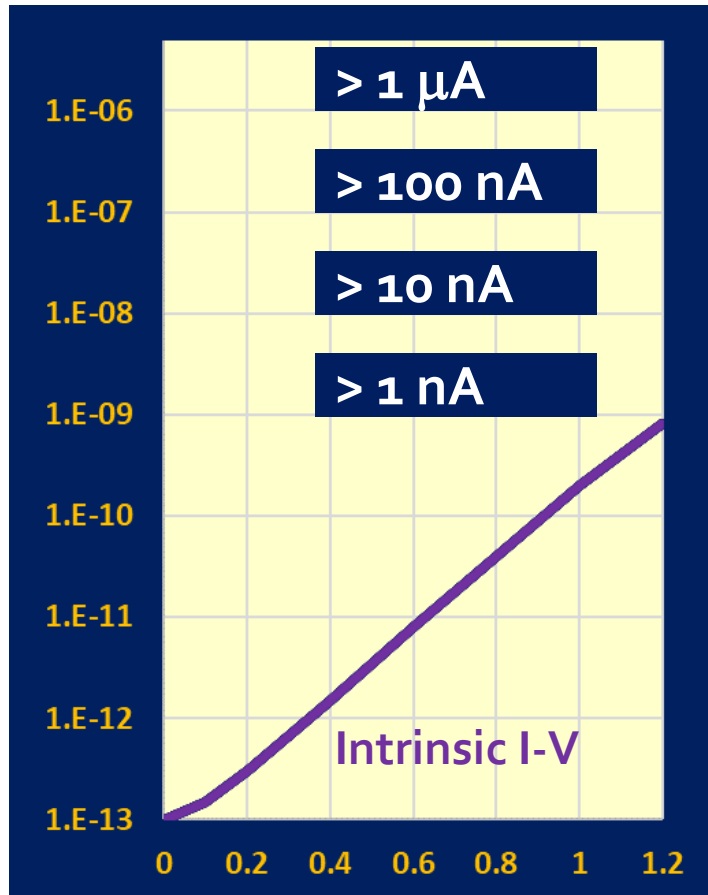
- DFI DUT quantity: 1B to 100B/wafer using in-product DFI fill cells
- In-die Reliability monitor: Focused DUT Design with DOE variants
- Reliability grading: Wafer and Die-level

DFI Scribe

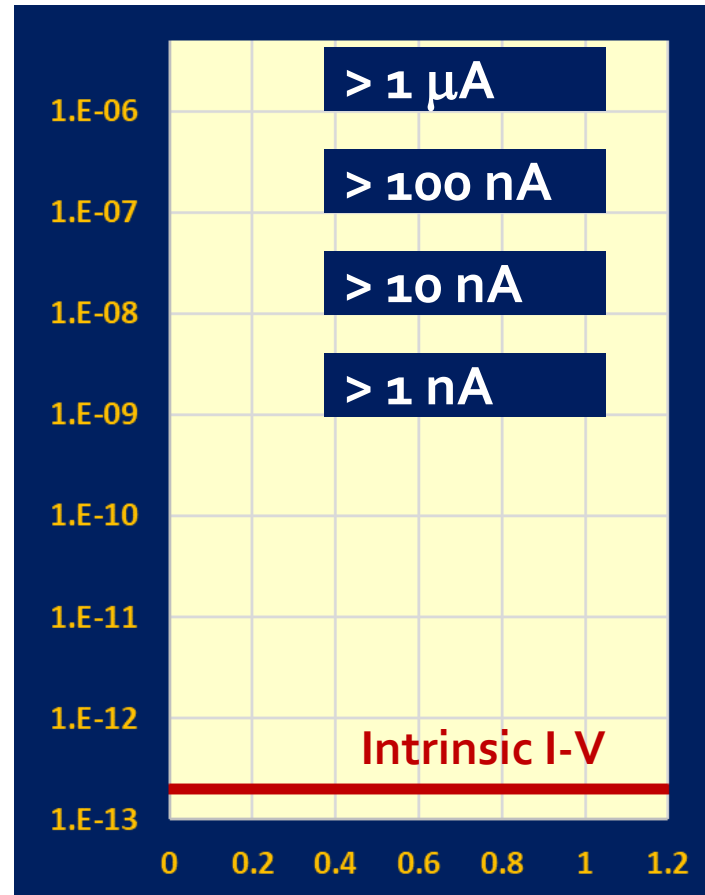
- DFI measurement density: 10-20M DUT's/mm² (product-like environment)
- Yield metrology: Misalignment, Process window, Root-cause Detection, Hot-spot/Defect monitor

Why Does Leakage Matter?

Gate Dielectric



Spacer, Contact/Metal Isolation



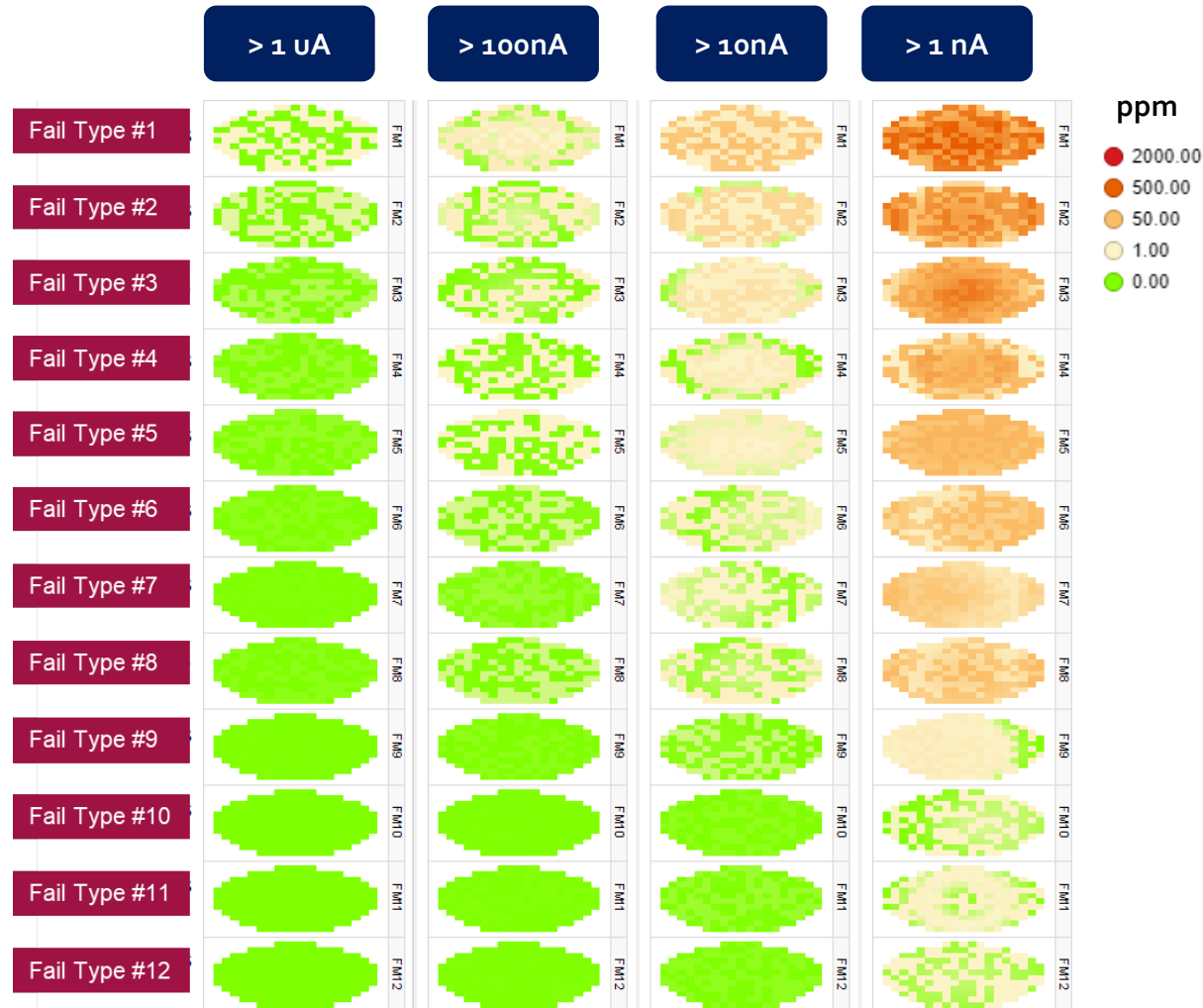
It is incredibly difficult to catch such tiny leakages in 10B's of transistors per chip

Leakage Outlier Bins
Identify Latent TDDDB
Weak Spots
RELIABILITY RISK

Typical Causes:

- Pinholes
- Dimensional Variation
- Process Damage
- Mechanical Stress

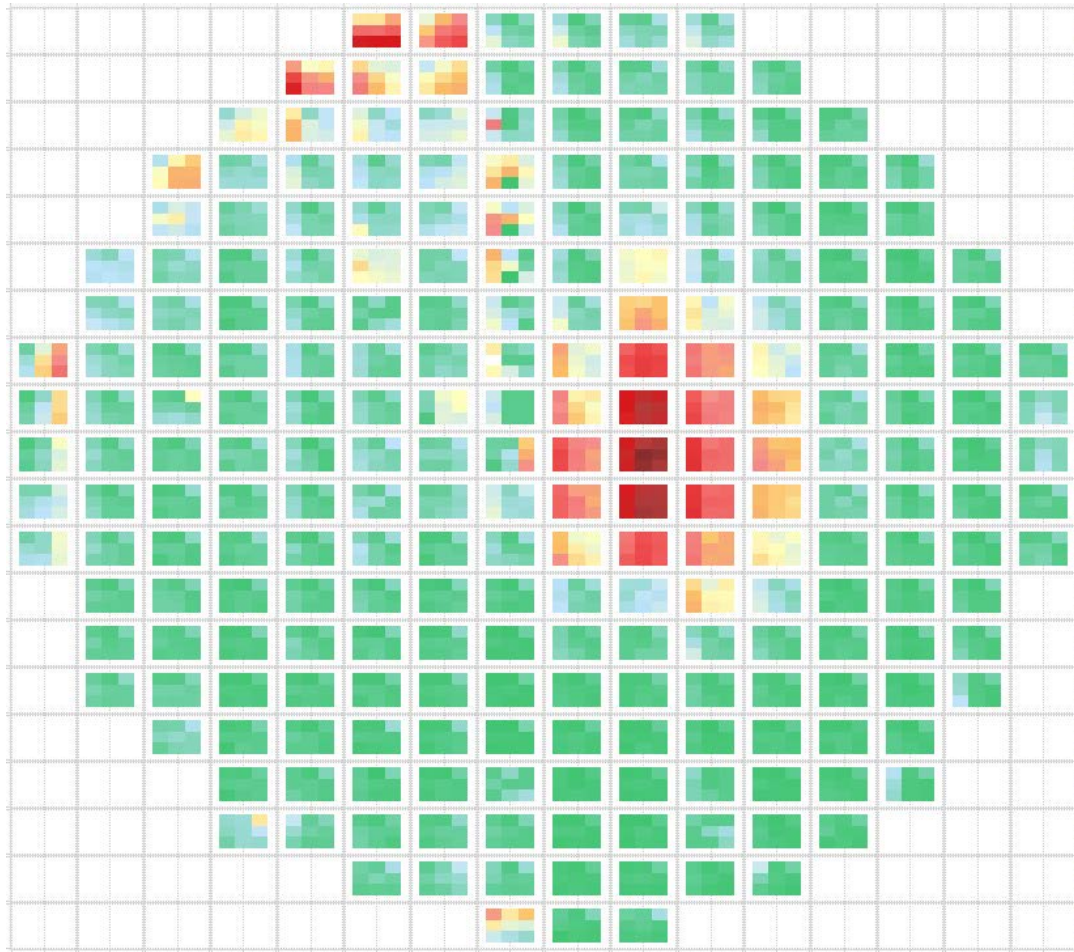
DFI™ Data: DUT Leakage Failure Rate Statistics



- Green die are zero ppm: Die with no failures observed
- Leakage level provides unique reliability insight into latent weak spots
- A composite of different fail mode estimates can indicate risk for early die failure or long term reliability

DFI *efficiently* scans billions of structures per wafer and catches tiny leakages at ppm to ppb levels, providing *early visibility* into potential *reliability risks*

DFI™ Die Control: Risk Grading



- High resolution map of every die for single fail type or composite of all fail types
- Spatial signature determines good/bad/risky die
- Within die perspective to assess risk for across field variability or local risk to certain fail type

Detailed across-die measurement creates *foresight* and enables better risk screening per die than gross methods such as GDBN (“Good Die Bad Neighborhood”)

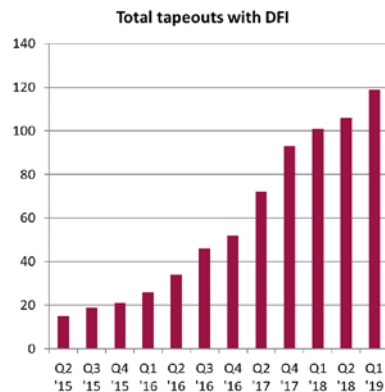
What is DFI™ status today?

eProbe® System



- eProbe® 150: Running in full automation in 3 R&D fabs
- eProbe® 250: 1st tool running in full automation in production fab

Silicon



- Over 100 tape-outs to date, spanning 6 nodes
- ~60 Product/MPW tape-outs with DFI content

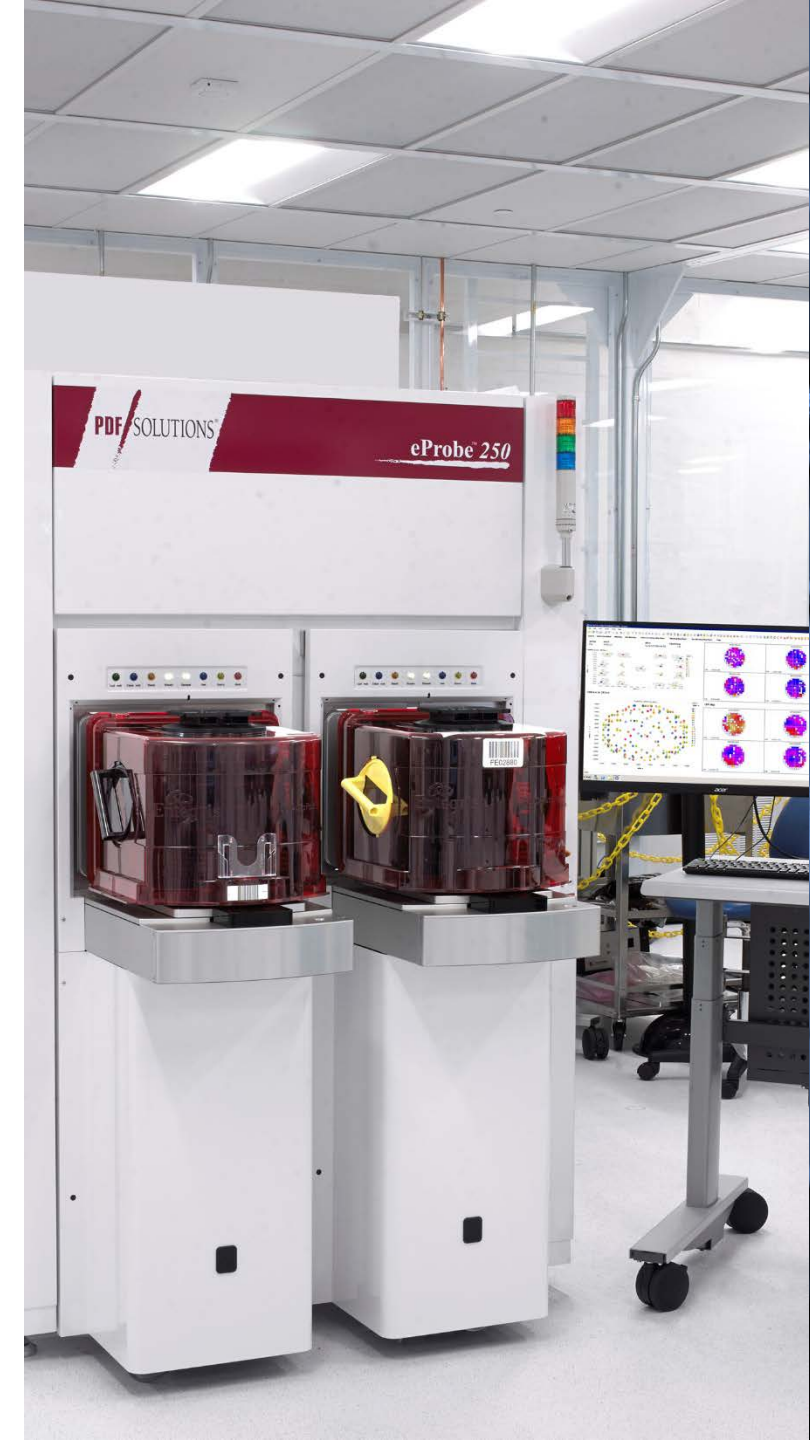
DFI™ Accomplishments 2019

eProbe® 150

- eProbe® 150 and Exensio DFI deployed at multiple sites using dense DFI test chips with throughput 10M's cells/hr
- In active use for yield learning on multiple nodes (22nm, 14nm, 7nm, 5nm)

eProbe® 250

- Demonstrated fill cell measurement throughput at 500M Cells/Hr
- Achieved first install in production fab complete with full automation
- Deployed for both scribe app and filler cell app at 7nm, 5nm in progress
- Demonstrated calibrated contactless leakage monitoring at DUT level
- Demonstrated applications for 3D NAND





Plenty of Work Remains!

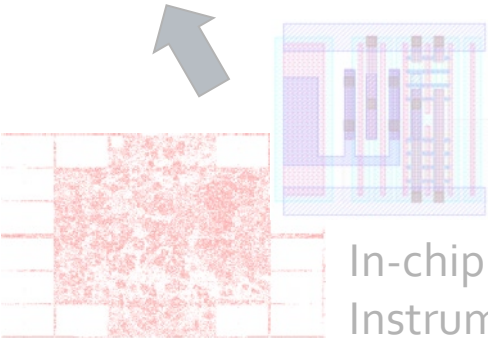
- Demonstrate production-worthy wafer level and die-level reliability grading app by leakage monitoring of critical fail modes
- Make DFI™ an essential element for fab control by providing insight into otherwise undetectable issues
- Expand applications of DFI™ into 3D NAND & other non-logic technology

PDF Differentiated Data for Reliability, Efficiency, and Foresight

Design-for-Inspection™ System



2nd generation
eProbe® 250
E-Beam HW

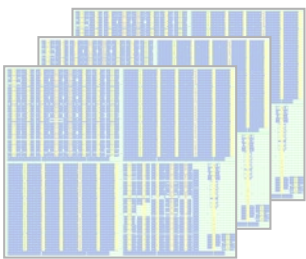


In-chip Product
Instruments

Characterization Vehicle® System

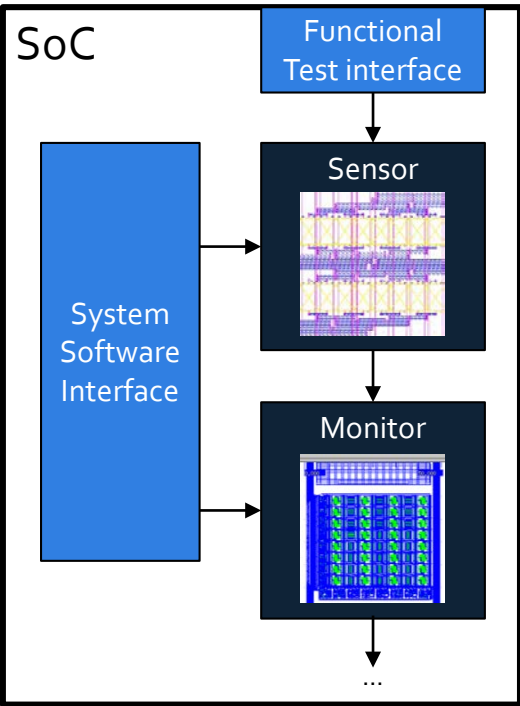


5th generation
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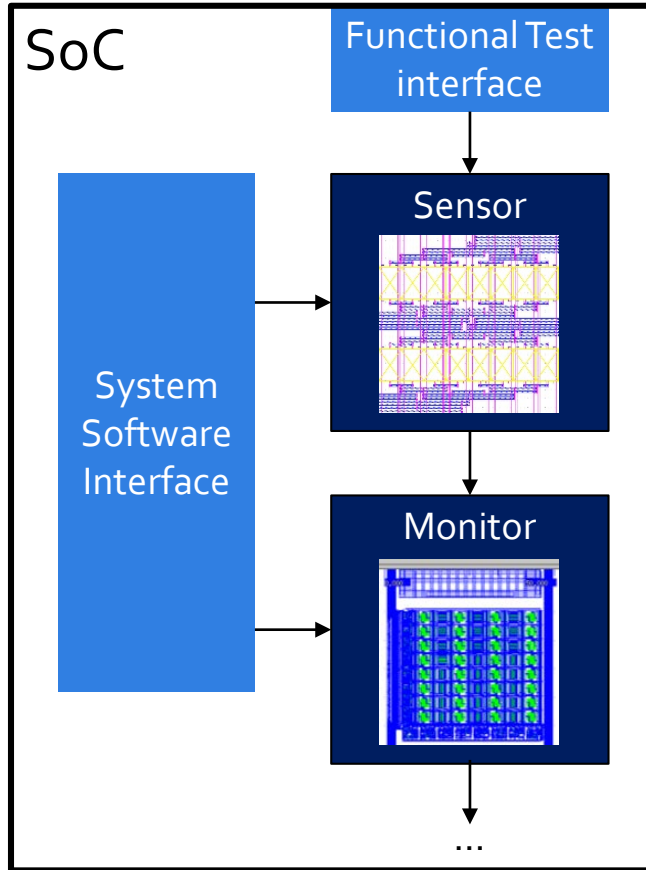


Inline

In-field

End-of-Line

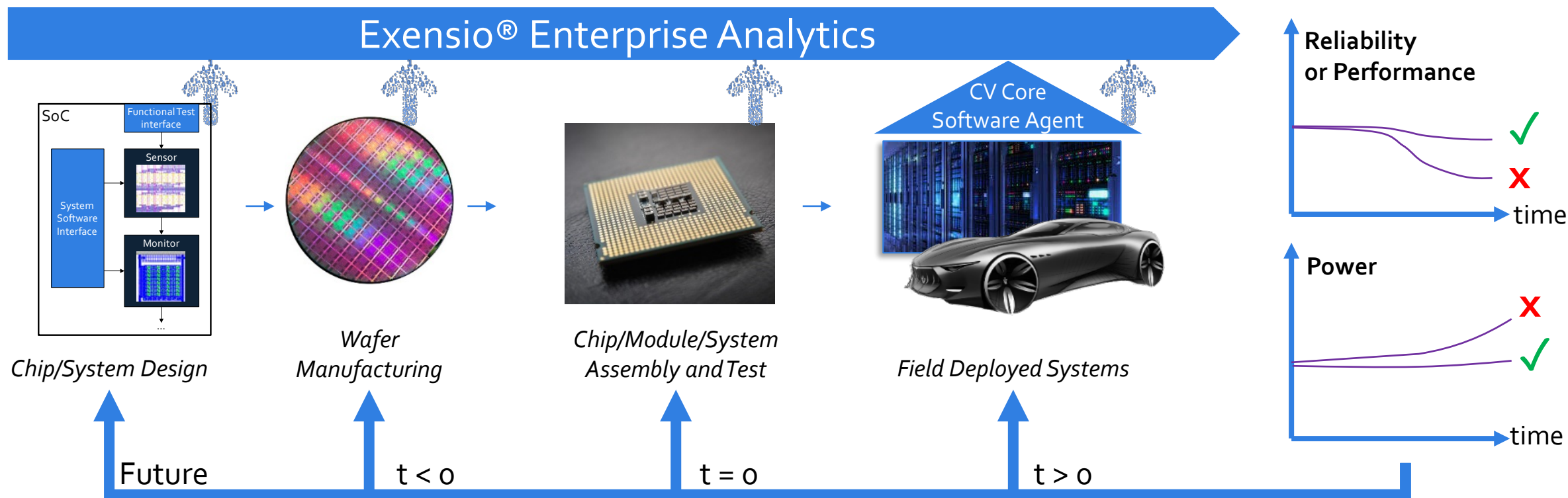
Leveraging IYR Technology: The CV[®] Core System



- The CV Core System integrates into your performance and reliability optimization strategy:
 - Capture weak die at t=0
 - Monitor Degradation in the field
 - Detect Change/Failure, Self Diagnosis, Failure Prediction
- PDF CV Core IP blocks are integrated using standard IP flows
 - GDS hard macro, LVS netlist, Verilog functional model, I/O spec
- The CV Core System enables:
 - Efficient t=0 reliability and performance screening
 - Mission mode t>0 reliability, performance monitoring, optimization
 - Seamless chip genealogy “From Fab to Field” for chip performance and reliability optimization across the complete product lifecycle



The CV[®] Core System



Optimize Next
Chip Design

Feedback Key Issues to
Manufacturing

Test Optimization

- Optimized flow
- Lower overall cost
- Improved Quality

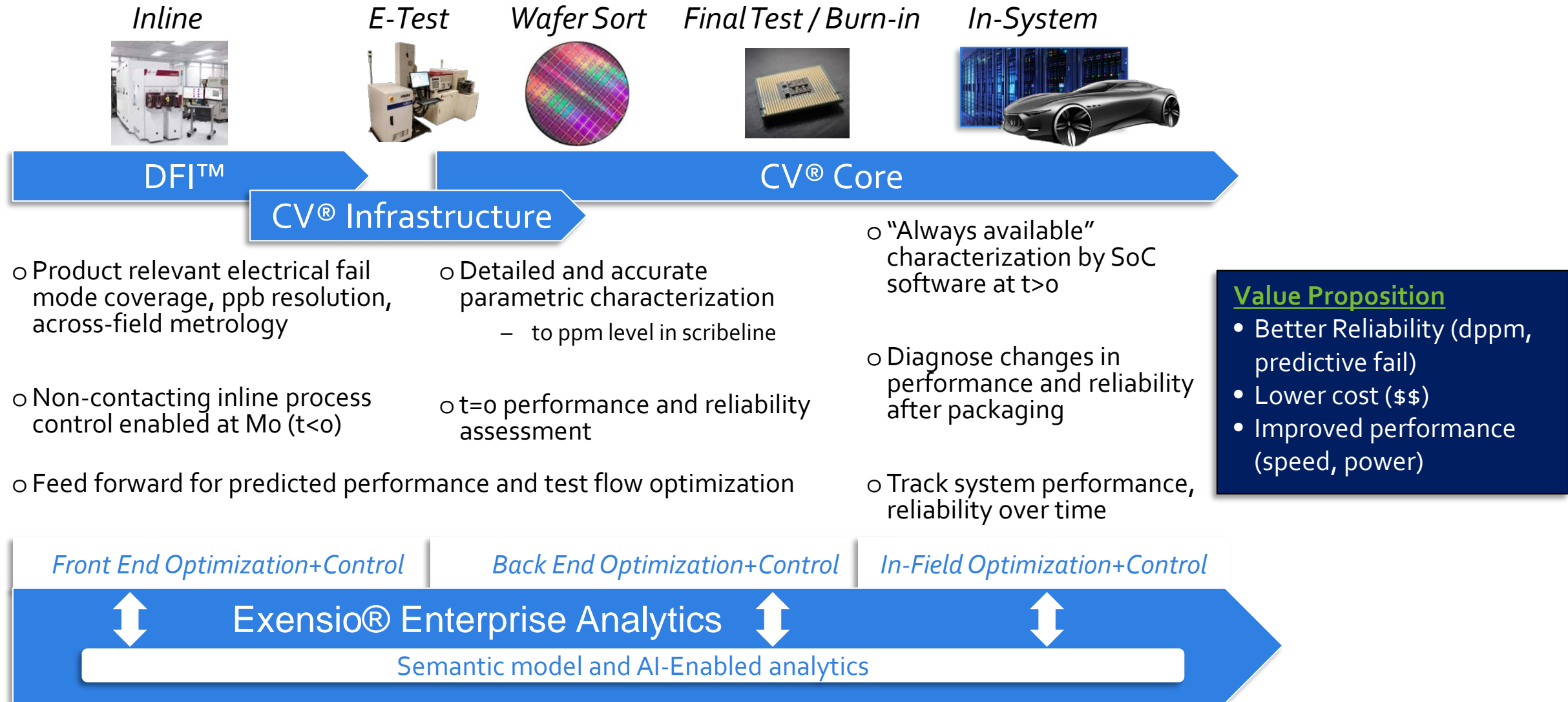
Runtime optimization

- Longer reliability
- Power/Perf vs. Reliability
- Failure prediction

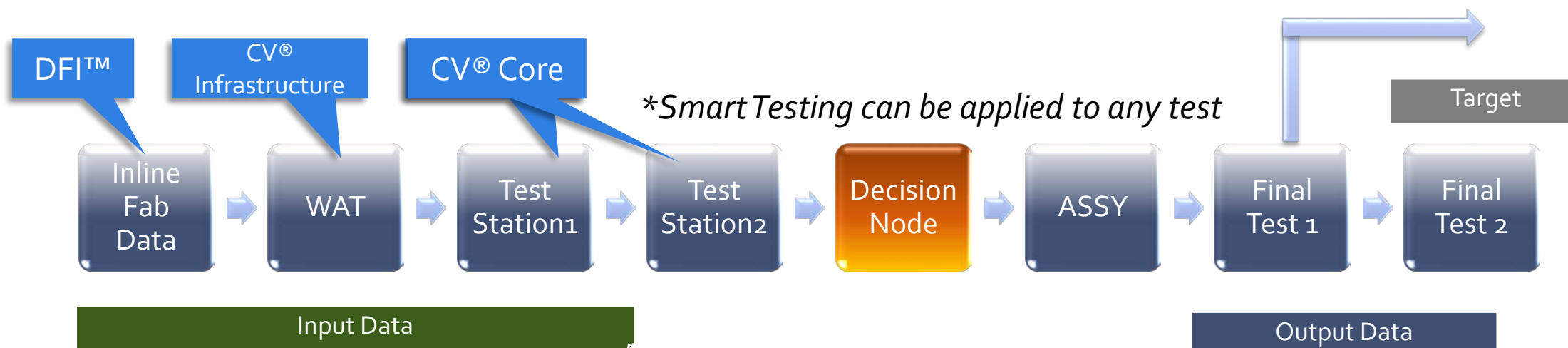
Value proposition (\$\$)

1. Greater reliability & predictive maintenance (uninterrupted service → \$)
2. Product optimization (MWh → \$)

PDF Differentiated Data Leverages Exensio® End-to-end Analytics

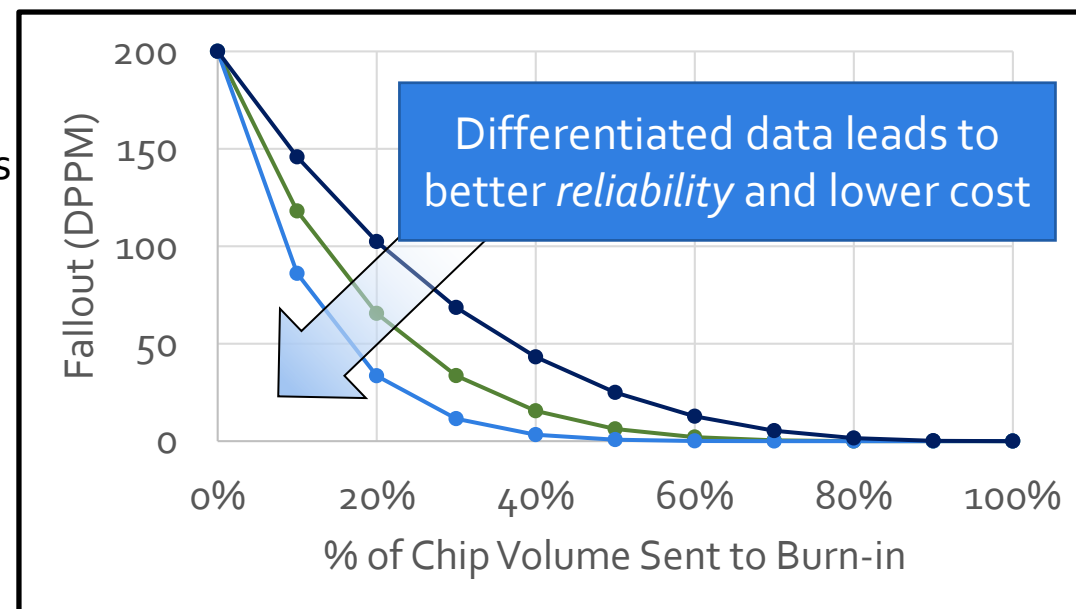


Smart Testing → Benefits from Differentiated Data



Goals:

- No risky chips to field, while diverting chips from expensive tests
- Improve quality and reliability by quickly identifying the root cause of field returns
- Focus test resources on product that are at the highest risk for failure
- Reduce test cost by diverting low-risk product volume away from expensive tests
- Smarter product binning by quality





Summary

- PDF's business has always been based on data
- Semiconductor system complexity continues to increase
- We continue to innovate new sources of data to efficiently improve reliability, performance, and yield, and reduce cost
- The Exensio® end-to-end analytics platform leverages this data to create *foresight* and optimize operational flows

Thank You

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